

### INCHANGE SEMICONDUCTOR

### **Isc N-Channel MOSFET Transistor**

### IPA60R385CP

#### FEATURES

- With TO-220F package
- · Low input capacitance and gate charge
- · Low gate input resistance
- Reduced switching and conduction losses
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

#### APPLICATIONS

Switching applications

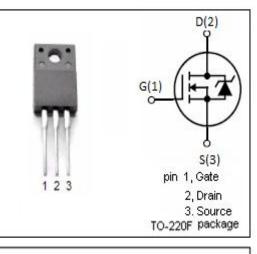
ABSOLUTE MAXIMUM RATINGS(Ta=25 C)						
SYMBOL	PARAMETER	VALUE	UNIT			
V <sub>DSS</sub>	Drain-Source Voltage	600	V			
V <sub>GSS</sub>	Gate-Source Voltage	±30	V			
ID	Drain Current-Continuous @Tc=25℃   (V <sub>GS</sub> at 10V) Tc=100℃	9.0 5.2	А			
I <sub>DM</sub>	Drain Current-Single Pulsed	27	А			
PD	Total Dissipation @Tc=25℃	31	W			
Tj	Max. Operating Junction Temperature	150	°C			
T <sub>stg</sub>	Storage Temperature	-55~150	°C			

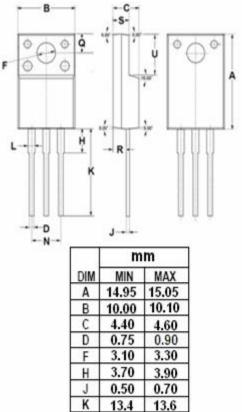
### • ABSOLUTE MAXIMUM RATINGS(T<sub>a</sub>=25℃)

#### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER		UNIT	
Rth(ch-c)	Channel-to-case thermal resistance	4.0	°C/W	
Rth(ch-a)	Channel-to-ambient thermal resistance	80	°C/W	

1





1.10

5.00

2.70

2.20

6.40

L

Ν

Q

R

5

1.30

5.20

2.90

2.40

2.90

6.60

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### **ELECTRICAL CHARACTERISTICS**

#### $T_{\text{C}}\text{=}25^{\circ}\!\!\!\!\mathrm{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	ТҮР	MAX	UNIT
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V; I <sub>D</sub> =0.25mA	600			v
V <sub>GS</sub> (th)	Gate Threshold Voltage	V <sub>DS</sub> = V <sub>GS</sub> ; I <sub>D</sub> =0.34mA	3.0		5.0	V
R <sub>DS(on)</sub>	Drain-Source On-Resistance	V <sub>GS</sub> = 10V; I <sub>D</sub> =5.2A		350	385	mΩ
I <sub>GSS</sub>	Gate-Source Leakage Current	V <sub>GS</sub> = ±20V;V <sub>DS</sub> =0V			±0.1	μA
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> = 600V; V <sub>GS</sub> = 0V;Tj=25℃ V <sub>DS</sub> = 600V; V <sub>GS</sub> = 0V; Tj=150℃			1 250	μA
V <sub>SDF</sub>	Diode forward voltage	I <sub>SD</sub> =5.2A, V <sub>GS</sub> = 0 V		0.9	1.2	V



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